

SCHOTTKY BARRIER DIODE

●Applications

Low current rectification and high speed switching

●Features

Extremely small surface mounting type. (SOD882)

High reliability

Low I_R .

●Construction

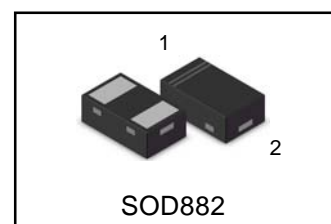
Silicon epitaxial planar

- We declare that the material of product compliance with RoHS requirements.

Ordering Information

Device	Marking	Shipping
LRB520BS-40T5G	D1	10000/Tape&Reel

LRB520BS-40T5G



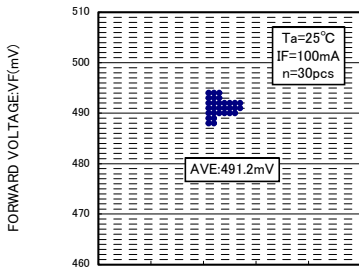
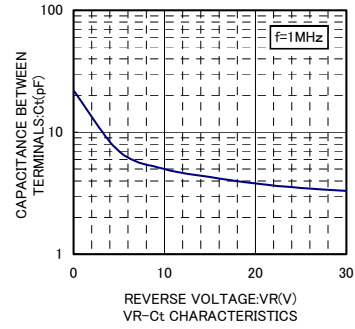
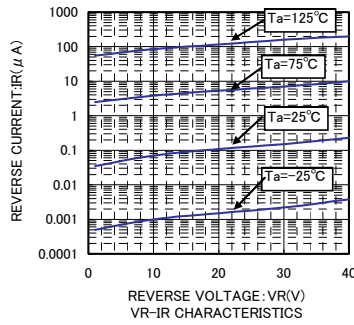
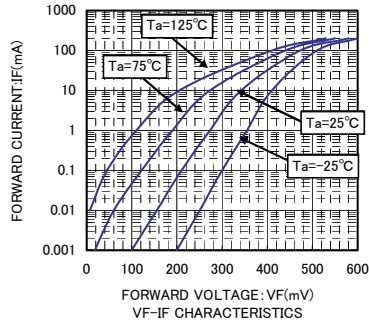
MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Reverse voltage(repetitive peak)	V_R	40	V
DC reverse voltage	V_R	40	V
Average rectified forward current	I_O	200	mA
Peak forward surge current	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40~+125	$^\circ\text{C}$

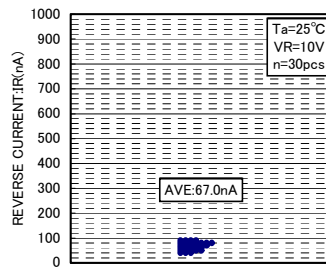
ELECTRICAL CHARACTERISTICS($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Max.	Unit	Conditions
Forward voltage	V_F	-	0.39	V	$I_F = 10\text{mA}$
Forward voltage	V_F	-	0.55	V	$I_F = 100\text{mA}$
Reverse current	I_R	-	1	μA	$V_R = 10\text{V}$
Reverse current	I_R	-	10	μA	$V_R = 40\text{V}$

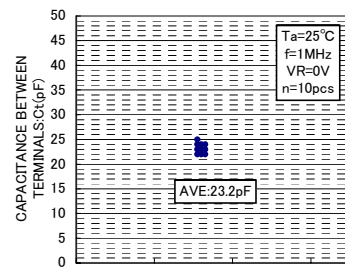
●Electrical characteristic curves



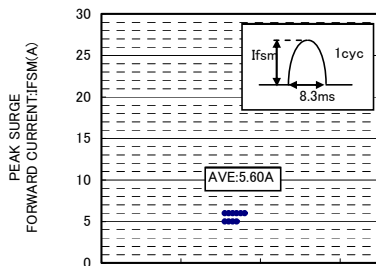
VF DISPERSION MAP



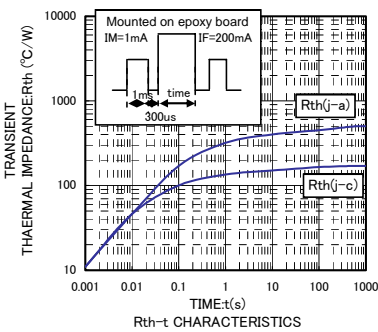
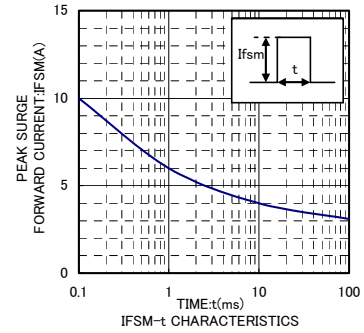
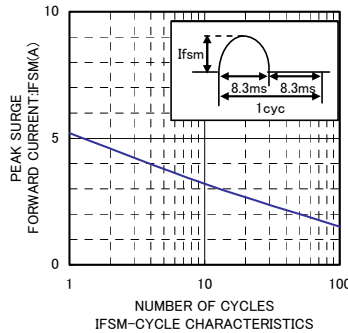
IR DISPERSION MAP



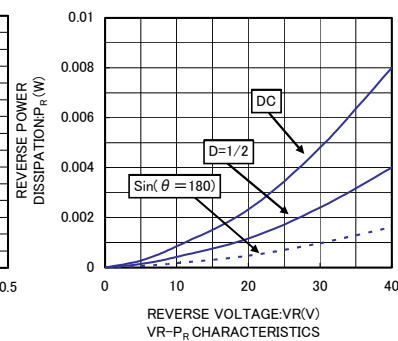
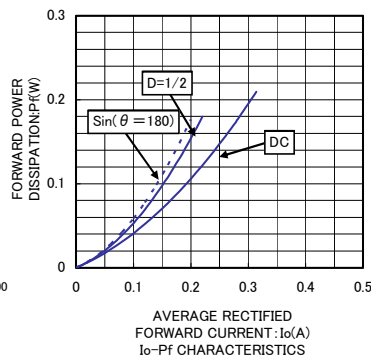
Ct DISPERSION MAP

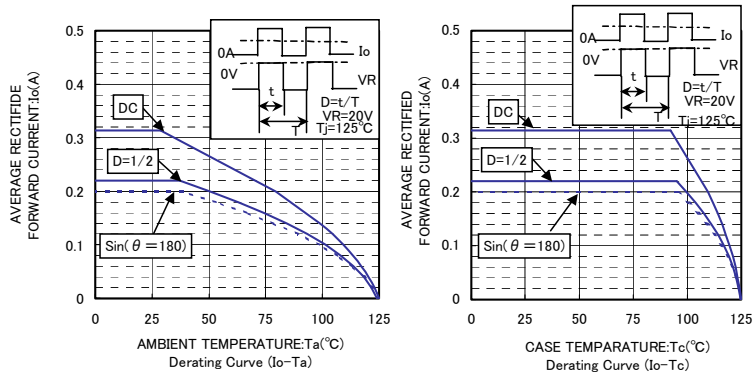


IFSM DISPERSION MAP



Rth-t CHARACTERISTICS



LRB520BS-40T5G


SOD882

DIMENSION OUTLINE:

Unit:mm

